Standard specifications of 100 mm β-Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

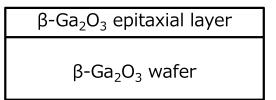
Items	Specifications
Dopant	Si (n-type)
Poping concentration *A value can be selected in increments of 1×10 ¹⁶ cm ⁻³ .	Specify a value in the range between 1×10^{16} and 9×10^{16} cm ⁻³
Thickness *A value can be selected in increments 1 µm.	Specify a value in the range between 5 and 10 µm

Wafer

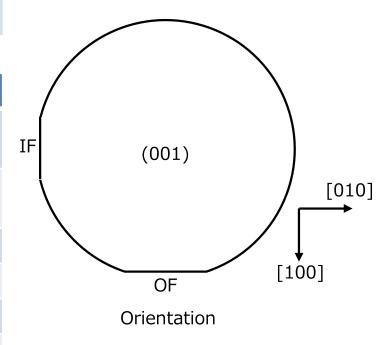
Items	Specifications
Dopant	Sn (n-type)
Resistivity	$0.007\sim 0.042~\Omega\cdot cm$
Orientation	(001)
Size	100 mm
Thickness	0.65 mm
XRD FWHM	≦350 arcsec
Off set angle	0°±1°

Remarks

- 1 There are cases in which the other side of OF is chipped (a maximum of around IF width).
- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.



Cross section of β -Ga₂O₃ epitaxial wafer





Novel Crystal Technology, Inc.

Standard specifications of 2 inch β-Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

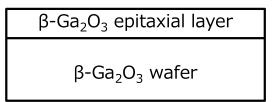
Items	Specifications
Dopant	Si (n-type)
Doping concentration *A value can be selected in increments of 1×10 ¹⁶ cm ⁻³ .	Specify a value in the range between 1×10^{16} and 9×10^{16} cm ⁻³
Thickness *A value can be selected in increments 1 µm.	Specify a value in the range between 5 and 10 µm

Wafer

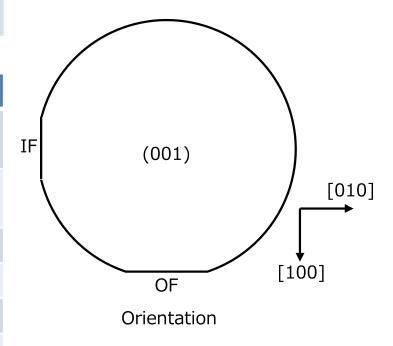
Items	Specifications
Dopant	Sn (n-type)
Resistivity	$0.007\sim 0.042~\Omega\cdot cm$
Orientation	(001)
Size	2 inch
Thickness	0.65 mm
XRD FWHM	≦350 arcsec
Off set angle	0°±1°

Remarks

- 1 There are cases in which the other side of OF is chipped (a maximum of around IF width).
- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.



Cross section of β -Ga₂O₃ epitaxial wafer





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